SHEET 1 OF 1

	9/3/03	>
7	6.01/10	_

INFORMATION DISCLOSURE CITATION			26615		ATTORNEY'S DKT NO. H1505 APPLICANT(S) Bin YU et al. FILING DATE September 3, 2003		APPLICATION No. Unassigned GROUP Unassigned					
_	PTO-1449						Chassigned					
U.S. PATENT DOCUMENTS												
EXAMINER'S INITIALS	PATENT NO.	DATE	<u> </u>	NAME		CLASS	SUBCLASS DATE					
		<u></u>			<u></u>							
	Y		FOREIGN PATEN	IT DO	CUMENTS	γ	1					
EXAMINER'S INITIALS	PATENT NO.	TENT NO. DATE		COUNTRY		CLASS	SUBCLASS	Yes	No			
	OTHER DOC	UMENTS		nor, Ti	tle, Date, Pert	inent Pag	es, Etc.)					
sec	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.											
	421-424.		'Sub-20nm CMC						3 S			
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.											
<u> </u>	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.											
ser	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.											
EXAMINER				DAT	E CONSIDERE	D						

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).